

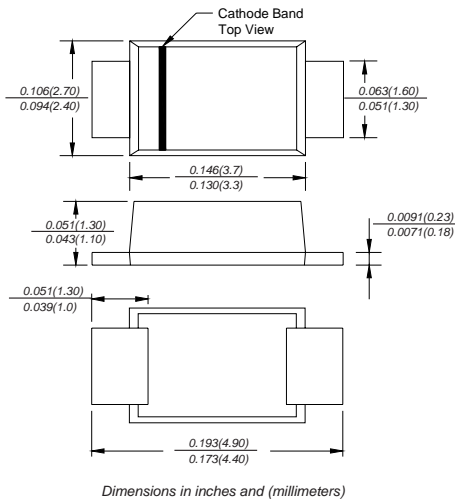


# SS12F THRU SS1200F

## SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts Forward Current - 1.0 Ampere

### SMAF



### FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Metal silicon junction, majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed: 260°C/10 seconds at terminals

### MECHANICAL DATA

**Case:** JEDEC SMAF molded plastic body  
**Terminals:** leads solderable per MIL-STD-750, Method 2026  
**Polarity:** Color band denotes cathode end  
**Mounting Position:** Any  
**Weight:** 0.0018 ounce, 0.064 grams

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

MDD Catalog Number	SYMBOLS	SS12F	SS13F	SS14F	SS15F	SS16F	SS18F	SS110F	SS1150F	SS1200F	UNITS	
Maximum repetitive peak reverse voltage	$V_{RRM}$	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum RMS voltage	$V_{RMS}$	14	21	28	35	42	56	70	105	140	VOLTS	
Maximum DC blocking voltage	$V_{DC}$	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum average forward rectified current at $T_L$ (see fig. 1)	$I_{(AV)}$	1.0									Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	30.0									Amps	
Maximum instantaneous forward voltage at 1.0A	$V_F$	0.55			0.70			0.85		0.95	Volts	
Maximum DC reverse current at rated DC blocking voltage	$I_R$	0.5							0.2		mA	
$T_A=25^\circ\text{C}$ $T_A=100^\circ\text{C}$		10.0				5.0			2.0			
Typical junction capacitance (NOTE 1)	$C_J$	110					90					pF
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	88.0										°C/W
Operating junction temperature range	$T_J$	-50 to +125						-50 to +150				°C
Storage temperature range	$T_{STG}$	-50 to +150										°C

**Note:** 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.  
 2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

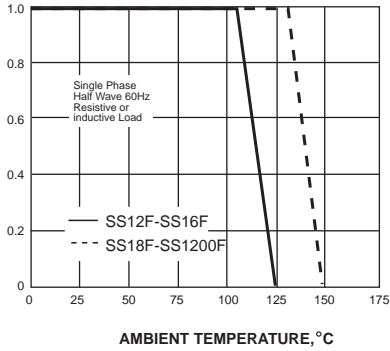


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# RATINGS AND CHARACTERISTIC CURVES SS12F THRU SS1200F

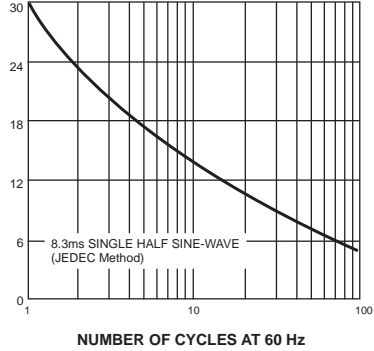
AVERAGE FORWARD RECTIFIED CURRENT,  
AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



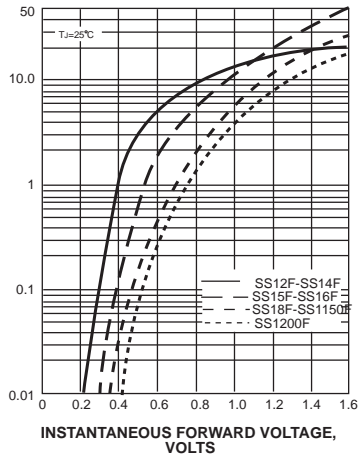
PEAK FORWARD SURGE CURRENT,  
AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



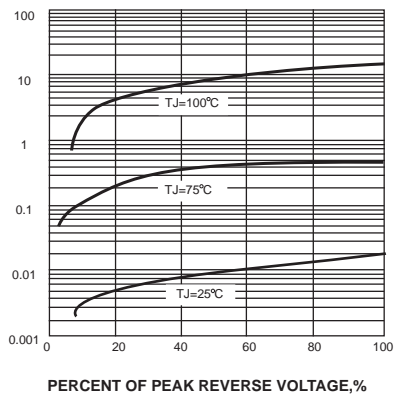
INSTANTANEOUS FORWARD CURRENT, AMPERES

FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



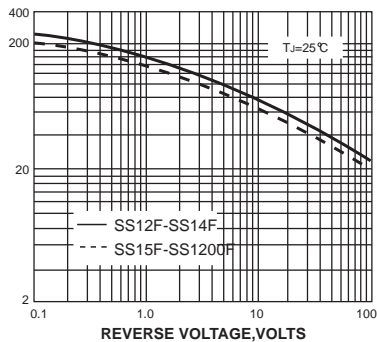
INSTANTANEOUS REVERSE CURRENT, MILLIAMPERES

FIG. 4-TYPICAL REVERSE CHARACTERISTICS



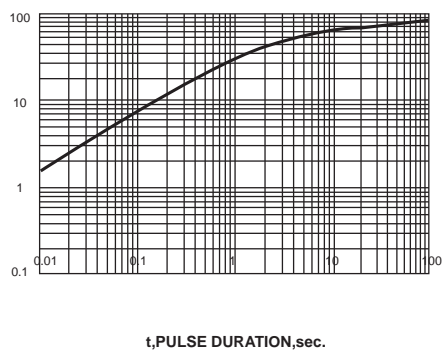
JUNCTION CAPACITANCE, pF

FIG. 5-TYPICAL JUNCTION CAPACITANCE



TRANSIENT THERMAL IMPEDANCE, °C/W

FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



The cruve graph is for reference only, can't be the basis for judgment(曲线图仅供参考)!

